

**In the Claims:**

Please rewrite claims 1-5 and 7-9 as follows:

1. (Currently Amended) A corrosion-resistive member, ~~comprising~~ having a corrosion-resistive face which is to be exposed to a corrosive gas causing ion bombardment, wherein at least a part of said corrosion-resistive member ~~comprising~~ comprises a sintered body of silicon nitride body having an open porosity of not more than 5%, and wherein said sintered silicon nitride sintered body constituting constitutes said corrosion-resistive face, said corrosion-resistive member having a characteristic that:

wherein if two auxiliary planes are formed by cutting the said corrosion-resistive member to intersect vertically with said corrosion-resistive face and to be located vertically with respect to each other, said two auxiliary planes satisfy the following an orientation index between said two auxiliary planes being not less than is in a range of 0.8 and not more than to 1.2, and the following an orientation index between the said corrosion-resistive face and each of the said auxiliary faces being is not less than 1.5-:

Orientation wherein said orientation index between the said two auxiliary planes satisfies the following formula:

$$= [I_{s1}(320)/(I_{s1}(320) + I_{s1}(002))] / [I_{s2}(320)/(I_{s2}(320) + I_{s2}(002))];$$

wherein  $I_{s1}(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in one "Is1" of the auxiliary planes;  $I_{s1}(002)$  denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes "Is1";  $I_{s2}(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the other auxiliary plane "Is2"; and  $I_{s2}(002)$  denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes "Is2"; and

Orientation wherein said orientation index between the said corrosion-resistive face and each of the said auxiliary planes satisfies the following formula:

$$= [I_m(320)/(I_m(320) + I_m(002))] / [I_s(320)/(I_s(320) + I_s(002))];$$

- 5 -

\_\_\_\_\_ wherein  $I_m(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the corrosion-resistive face " $m$ ";  $I_m(002)$  denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the corrosion-resistive face " $m$ ";  $I_s(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the auxiliary plane " $s$ "; and  $I_s(002)$  denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes " $s$ ".

2. (Currently Amended) A corrosion-resistive member having a corrosion-resistive face which is exposed to a corrosive gas causing ion bombardment, wherein at least a part of said corrosion-resistive member comprises a sintered silicon nitride body having an open porosity of not more than 5%. The corrosion-resistive member set forth in claim 1, wherein the total content of elements in Group Ia and Groups 4a - 3b of the Periodic Table present in the said sintered silicon nitride sintered-body is not more than 50 ppm by weight, and wherein said sintered silicon nitride body constitutes said corrosion-resistive face;

wherein if two auxiliary planes are formed by cutting said corrosion-resistive member to intersect vertically with said corrosion-resistive face and to be located vertically with respect to each other, an orientation index between said two auxiliary planes is in a range of 0.8 to 1.2, and an orientation index between said corrosion-resistive face and each of said auxiliary faces is not less than 1.5;

wherein said orientation index between the two auxiliary planes satisfies the following formula:

$$\frac{[I_s(320)/(I_s(320) + I_s(002))]/[I_s(320)/(I_s(320) + I_s(002))]}{[I_s(320)/(I_s(320) + I_s(002))]/[I_s(320)/(I_s(320) + I_s(002))]};$$

wherein  $I_s(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in one " $s$ " of the auxiliary planes;  $I_s(002)$  denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes " $s$ ";  $I_s(320)$  denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the other auxiliary plane " $s$ "; and

- 6 -

Is2(002) denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes "Is2"; and

wherein said orientation index between said corrosion-resistive face and each of said auxiliary planes satisfies the following formula:

$$\frac{Im(320)/(Im(320) + Im(002))}{[Is(320)/(Is(320) + Is(002))]};$$

wherein Im(320) denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the corrosion-resistive face "m"; Im(002) denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the corrosion-resistive face "m"; Is(320) denotes an intensity of X-ray diffraction at a 320 face of  $\beta$ -type silicon nitride in the auxiliary plane "Is"; and Is(002) denotes an intensity of X-ray diffraction at a 002 face of  $\beta$ -type silicon nitride in the auxiliary planes "Is".

3. (Currently Amended) The corrosion-resistive member set forth in claim 1, wherein one or more metal elements selected from Group 2a and Group 3a in the Periodic Table are ~~contained~~ present in a total amount of 1 to 15 mol% in said ~~sintered~~ silicon nitride ~~sintered~~-body as calculated externally in the form of the metal ~~element(s)~~ elements relative to said silicon nitride.

4. (Currently Amended) The corrosion-resistive member set forth in claim 3, wherein ~~the said sintered~~ silicon nitride ~~sintered~~-body further comprises one or more elements selected from the group consisting of calcium, strontium, barium, magnesium, yttrium and lanthanoids ~~lanthanoid~~ elements.

5. (Currently Amended) The corrosion-resistive member set forth in claim 4, wherein said ~~sintered~~ silicon nitride ~~sintered~~-body comprises one or more elements selected from the group consisting of magnesium, yttrium, cerium, samarium and lanthanum.

6. (Previously Presented) The corrosion-resistive member set forth in claim 3, wherein at least one of said one or more metal elements selected from

Group 2a and Group 3a in the Periodic Table is in the form of an oxide.

7. (Currently Amended) The corrosion-resistive member set forth in claim 1, ~~which wherein said corrosion-resistive member~~ has a thermal conductivity of 50 W/m·K or less.

8. (Currently Amended) The corrosion-resistive member set forth in claim 1, wherein ~~the-said~~ corrosive gas is a halogen-based corrosive gas or a plasma of the ~~said~~ halogen-based corrosive gas.

9. (Currently Amended) A semiconductor-producing article comprising a substrate comprising the-said corrosion-resistive member set forth in claim 1 as a substrate.

**Please add new claims 10-16 as follows:**

10. (New) The corrosion-resistive member set forth in claim 2, wherein one or more metal elements selected from Group 2a and Group 3a in the Periodic Table are present in a total amount of 1 to 15 mol% in said sintered silicon nitride body as calculated externally in the form of the metal elements relative to said silicon nitride.

11. (New) The corrosion-resistive member set forth in claim 10, wherein said sintered silicon nitride body further comprises one or more elements selected from the group consisting of calcium, strontium, barium, magnesium, yttrium and lanthanoid elements.

12. (New) The corrosion-resistive member set forth in claim 11, wherein said sintered silicon nitride body comprises one or more elements selected from the group consisting of magnesium, yttrium, cerium, samarium and lanthanum.

13. (New) The corrosion-resistive member set forth in claim 10, wherein

- 8 -

at least one of said one or more metal elements selected from Group 2a and Group 3a in the Periodic Table is in the form of an oxide.

14. (New) The corrosion-resistive member set forth in claim 2, wherein said corrosion-resistive member has a thermal conductivity of 50 W/m·K or less.

15. (New) The corrosion-resistive member set forth in claim 2, wherein said corrosive gas is a halogen-based corrosive gas or a plasma of said halogen-based corrosive gas.

16. (Currently Amended) A semiconductor-producing article comprising a substrate comprising said corrosion-resistive member set forth in claim 2.